

- **Simple NMOS CM:**

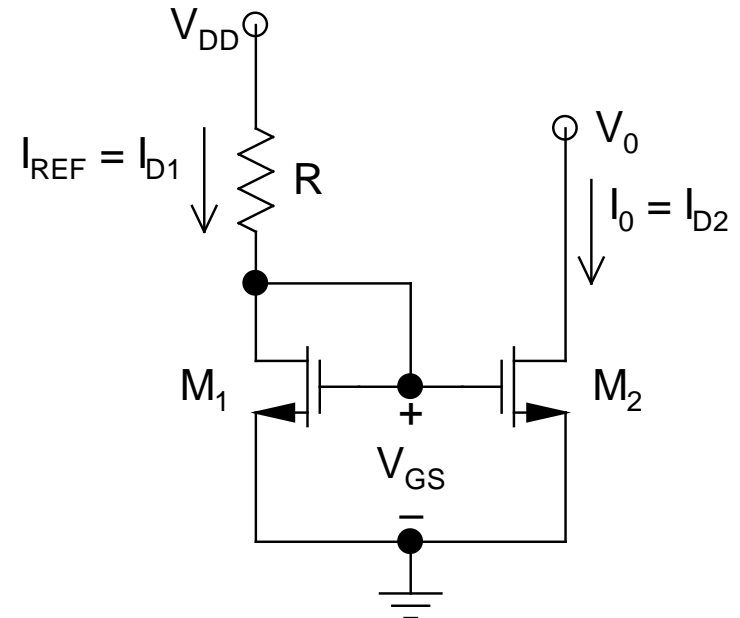
- $V_{GS1} = V_{GS2} = V_{GS}$

- $M_1$  has its ***D and G***  
***shorted***  $\Rightarrow V_{GD1} = 0$

$\Rightarrow$  ***always in saturation***,  
since  $V_{DS1} > V_{GT1}$

$\Rightarrow$  Known as ***diode-***  
***connected MOSFET***

- Even though  $I_G = 0$ , the analysis is slightly more cumbersome than simple BJT CM



➤ *In general, for NMOS (PMOS), the body terminal is always connected to the most negative (positive) potential available in the circuit to ensure that SB and DB junctions never get forward biased*

➤ *Both  $M_1$  and  $M_2$  have their body terminals grounded  $\Rightarrow V_{SB1} = V_{SB2} = 0$*

▪  $V_{TN1} = V_{TN01}$  and  $V_{TN2} = V_{TN02}$

➤ Thus, neglecting CLM:

$$I_{REF} = I_{D1} = \frac{k'_{N1}}{2} \left( \frac{W}{L} \right)_1 (V_{GS} - V_{TN01})^2$$

- For a *given  $V_{DD}$  and  $R$* , the equation has *2 unknowns*:  $I_{D1}$  and  $V_{GS}$
- Need *another equation* for *unique solution*, which is the *load line equation*:

$$I_{D1} = (V_{DD} - V_{GS})/R$$

- *Simultaneous solution* of these *two equations* would give a *unique solution* for  $I_{D1}$  and  $V_{GS}$ 
  - *Caution: 2 roots, out of which, one will be unphysical*
- So far, we have *neglected CLM*, which we would include soon!

➤ Now:

$$V_{GS} = V_{TN01} + \sqrt{\frac{2I_{REF}}{k'_{N1} (W/L)_1}} = V_{TN02} + \sqrt{\frac{2I_0}{k'_{N2} (W/L)_2}}$$

➤ Thus:

$$I_0 = \frac{k'_{N2} (W/L)_2}{2} \left[ (V_{TN01} - V_{TN02}) + \sqrt{\frac{2I_{REF}}{k'_{N1} (W/L)_1}} \right]^2$$

➤ This is the *exact expression* of  $I_0$ , *without making any assumptions/approximations whatsoever*

➤ Now, if  $V_{TN01} = V_{TN02} = V_{TN0}$ , and

$$k'_{N1} = k'_{N2} = k'_N :$$

$$I_0 = \frac{(W/L)_2}{(W/L)_1} I_{REF}$$

➤ *Very similar* to BJT CM, but with a *big difference*:

- *In BJT CM, this ratio could only be an integer*
- *In MOS CM, no such restriction exists:  $(W/L)_2$  can be  $>$ ,  $=$ , or  $<$   $(W/L)_1 \Rightarrow$  any arbitrary current ratio can be obtained*

➤ Finally, if  $(W/L)_2 = (W/L)_1$ :

$$I_0 = I_{\text{REF}} \Rightarrow \text{Current Mirror!}$$

➤ Two MOSFETs are deemed to constitute a *matched pair*, if they have *same*  $V_{\text{TN0}}$ ,  $\gamma$ ,  $\phi_{\text{F}}$ ,  $\lambda$ , and  $k'_{\text{N}}$

- Note that all of these are *process parameters*
- *(W/L) is NOT a process parameter*, since it's under *designer's control*
- *If (W/L)s are also same, then the pair is known as perfectly matched*

- ***Systematic Error:***

- Even if  $M_1$  and  $M_2$  are *perfectly matched*, still  $I_0$  *may not equal*  $I_{REF}$ !

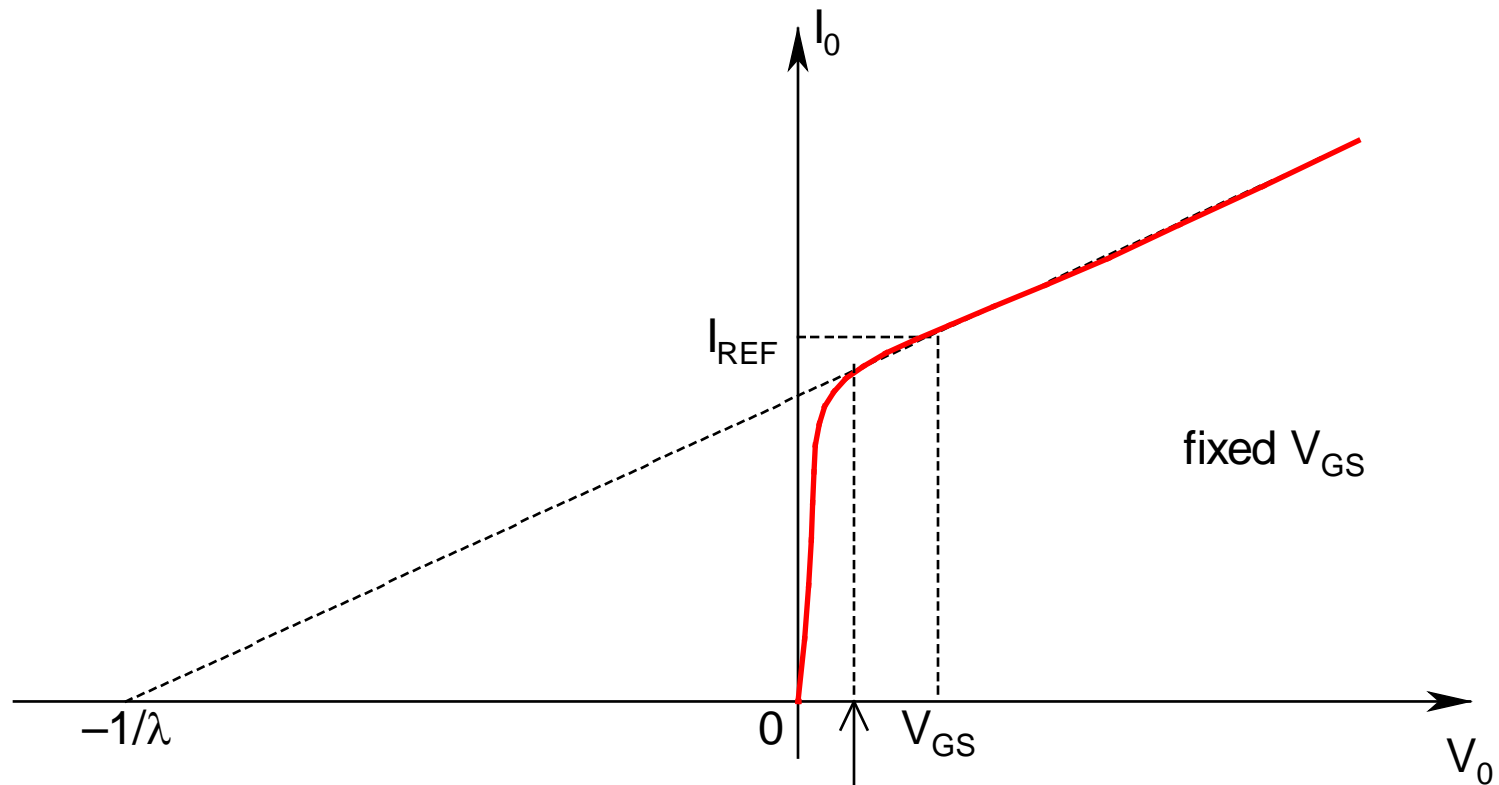
- Recall:

$$I_D = \frac{k_N}{2} V_{GT}^2 (1 + \lambda V_{DS})$$

- Thus:

$$\frac{I_0}{I_{REF}} = \frac{1 + \lambda V_{DS2}}{1 + \lambda V_{DS1}} = \frac{1 + \lambda V_0}{1 + \lambda V_{GS}}$$

- Therefore,  ***$I_0 = I_{REF}$  only when  $V_0 = V_{GS}$***

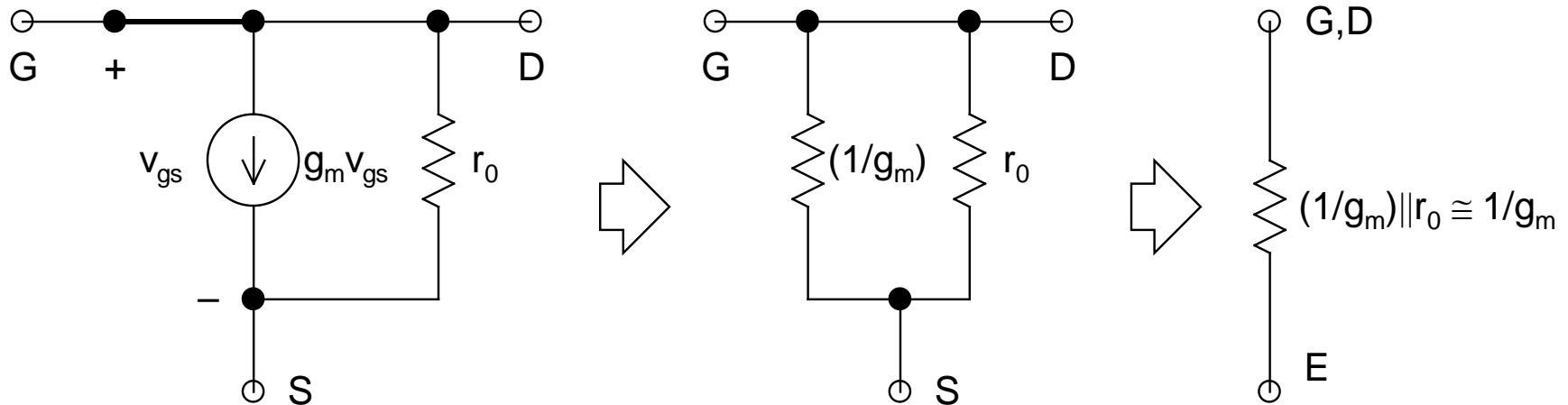


**$V_{o,min} = V_{DS2}(sat)$   
(lowest allowed  
value  $\approx 3V_T$ )**



- **Output Resistance  $R_o$ :**

➤ First, *investigate  $M_1$*



- The *small-signal equivalent* consists simply of  $1/g_m$ , which is similar to  $r_D$  for **diodes**
- Hence the name *diode-connected transistor*

- *For the complete circuit:*

- *Left part of the circuit has no source*

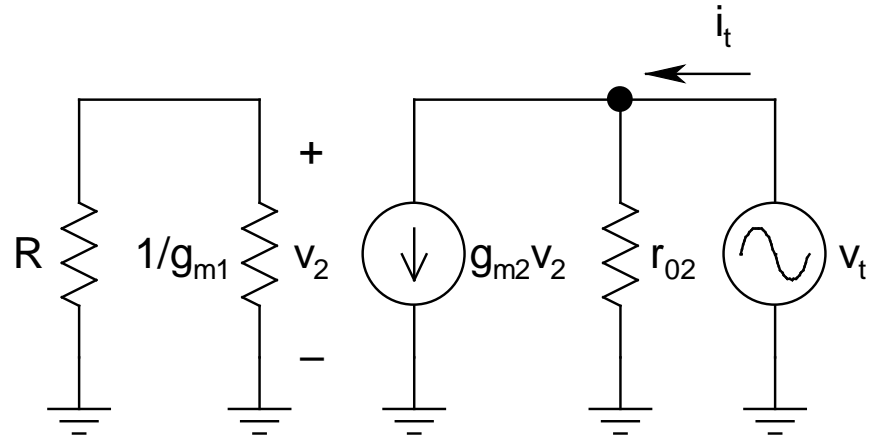
$$\Rightarrow v_2 = 0$$

$$\Rightarrow g_{m2}v_2 = 0$$

- Thus,  $R_0 = v_t/i_t = r_{o2} = 1/(\lambda I_0)$

- For a *good current source*,  $R_0$  should be as large as possible (*ideally infinite*)

$\Rightarrow \lambda$  should be as small as possible and/or  $I_0$  should be as small as possible



- *Golden Rule for Calculation of  $R_o$ :*

- For a *BJT* (or *MOSFET*):

- With Emitter (or Source) *grounded*
- *No electrical connection (feedback)* between Collector (or Drain) and Base (or Gate)
- *Looking from* the Collector (or Drain)
  - ❖ *The only resistance seen will be the output resistance of the BJT (or MOSFET)*

- ***npn Current Repeater:***

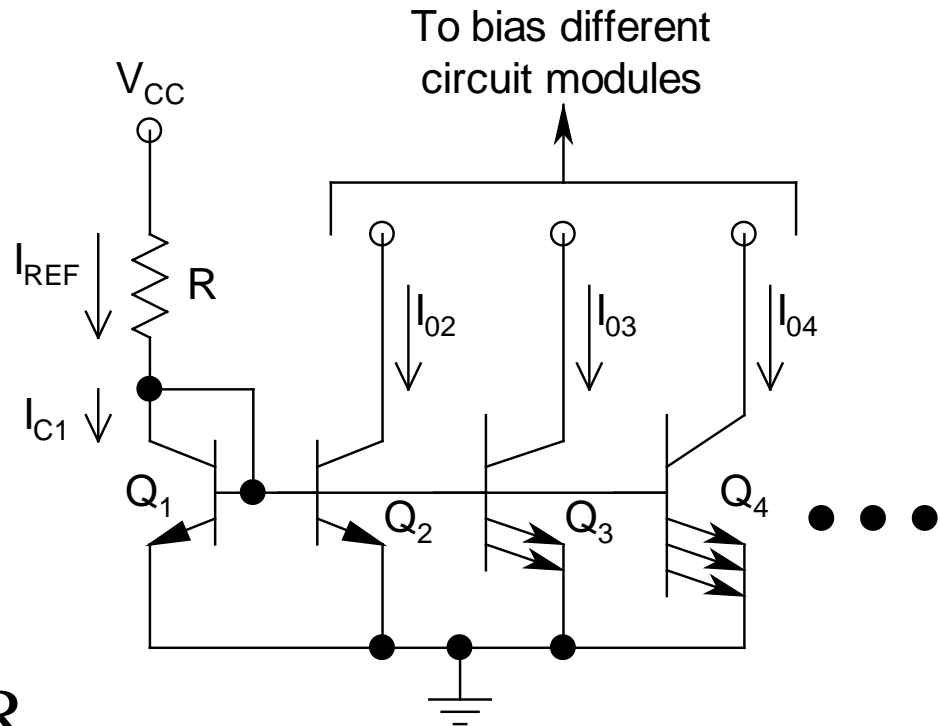
- *Uses multi-emitter BJTs*

- *Maximum number of emitters = 4*

- *All emitters tied together*

- *All  $Q$ s have same  $V_{BE}$*

- $I_{REF} = (V_{CC} - V_{BE})/R$



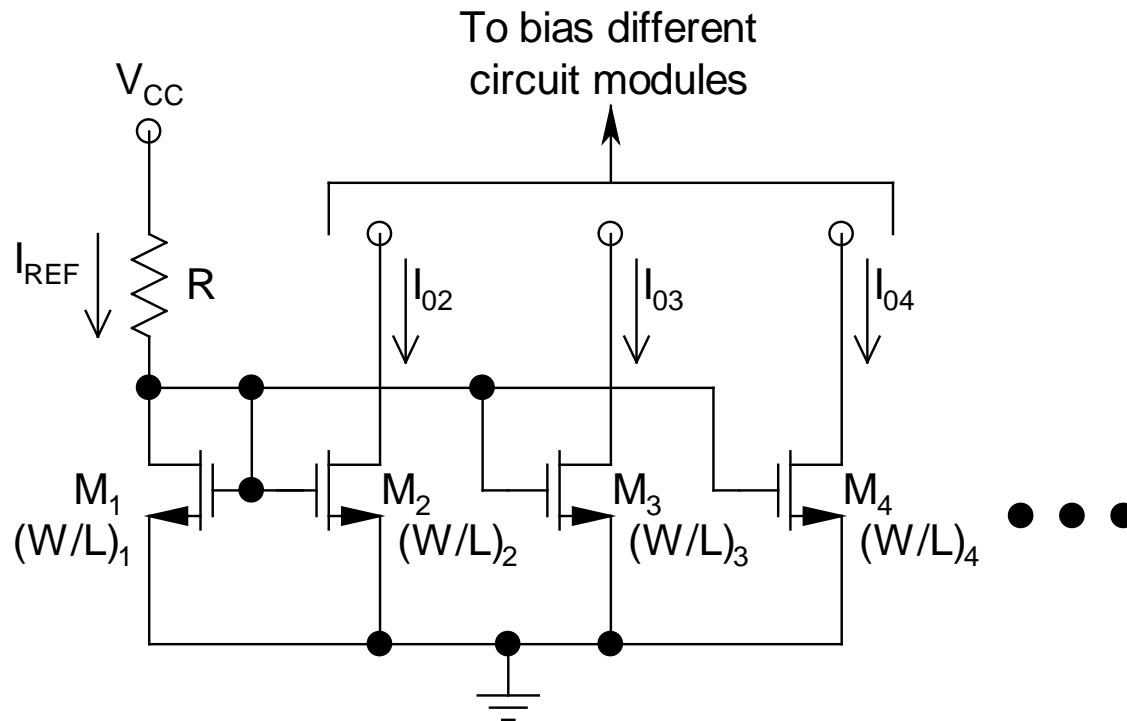
➤ *Neglecting  $I_B$ :*

$$I_{02} = I_{REF}, I_{03} = 2I_{REF}, I_{04} = 3I_{REF}, \dots$$

➤ *Limitations:*

- *Output current can never be a non-integer ratio of  $I_{REF} \Rightarrow$  no arbitrary scaling possible*
- *Loading Problem:*
  - ❖  *$I_{REF}$  not only supplies  $I_{C1}$ , but  $I_B$ s of all the  $Q$ s*
  - ❖ *As more  $Q$ s are added,  $I_B$ s will keep on increasing*
  - ❖  *$I_{C1}$  starts to depart significantly from  $I_{REF}$*
  - ❖ *It's actually NOT  $I_{REF}$  that's mirrored, BUT it's  $I_{C1}$*
  - ❖ *A reduction in  $I_{C1}$  will affect all output currents*
  - ❖ *Hence, this circuit is not very popular*

- ***NMOS Current Repeater:***



➤  $I_{\text{REF}} = I_{\text{D1}} = (V_{\text{DD}} - V_{\text{GS}})/R$

$$I_{\text{D1}} = \frac{k'_N}{2} \left( \frac{W}{L} \right)_1 V_{\text{GT}}^2 \quad (\text{assuming } \lambda V_{\text{DS}} < 0.1)$$

➤ *All Ms have same  $V_{\text{GS}}$  and are matched*

$$\Rightarrow I_{\text{oi}} = \frac{(W/L)_i}{(W/L)_1} I_{\text{REF}} \quad (i = 2, 3, 4, \dots)$$

➤ *Tremendous flexibility*

❖ *Any arbitrary current ratio can be obtained*

❖ *No loading effect*

❖ *Highly popular and universal choice*